

TMN10003MI

N-Channel Enhancement Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

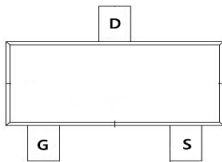
- Load switch
- PWM

General Features

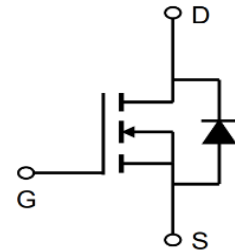
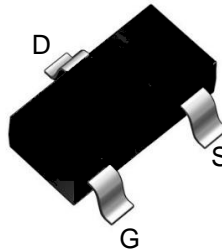
$V_{DS} = 100V$ $I_D = 3.0A$

$R_{DS(ON)} = 200m\Omega$ (typ.)@ $V_{GS}=10V$

100% UIS Tested
 100% R_g Tested



MI:SOT-23-3L



Marking: 3N10 OR 1002

Absolute Maximum Ratings (TC=25°C unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	3	A
$I_D @ T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	1.2	A
I_{DM}	Pulsed Drain Current ²	5	A
$P_D @ T_A=25^\circ C$	Total Power Dissipation ³	1	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	125	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	80	°C/W

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\mu\text{A}$	100	-	-	V
Gate Leakage Current	I_{GSS}	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$	-	-	± 100	nA
Drain Cut-off Current	I_{DSS}	$V_{DS} = 100\text{V}, V_{GS} = 0\text{V}$	-	-	1	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	1.1	1.5	2.5	V
Drain-Source on-state Resistance ³	$R_{DS(on)}$	$V_{GS} = 10\text{V}, I_D = 2\text{A}$	-	200	230	m Ω
		$V_{GS} = 4.5\text{V}, I_D = 1.5\text{A}$	-	220	280	
Dynamic Characteristics⁴						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 50\text{V},$ $f = 1\text{MHz}$	-	440	-	pF
Output Capacitance	C_{oss}		-	14	-	
Reverse Transfer Capacitance	C_{rss}		-	10	-	
Switching Characteristics⁴						
Total gate charge	Q_g	$V_{GS} = 10\text{V}, V_{DS} = 50\text{V},$ $I_D = 2\text{A}$	-	5.3	-	nC
Gate-source charge	Q_{gs}		-	1.4	-	
Gate-drain charge	Q_{gd}		-	1.8	-	
Turn-on Time	$t_{d(on)}$	$V_{GS} = 10\text{V}, V_{DD} = 50\text{V},$ $R_G = 1\Omega, I_D = 2\text{A}$	-	14	-	ns
Rise time	t_r		-	54	-	
Turn-off Time	$t_{d(off)}$		-	18	-	
Fall time	t_f		-	11	-	
Source-Drain Diode characteristics						
Body Diode Voltage ³	V_{SD}	$I_S = 1\text{A}, V_{GS} = 0\text{V}$	-	-	1.2	V
Continuous Source Current	I_S		-	-	3.0	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^{\circ}\text{C}$.
2. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
3. Pulse Test: Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
4. This value is guaranteed by design hence it is not included in the production test.

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Typical Characteristics

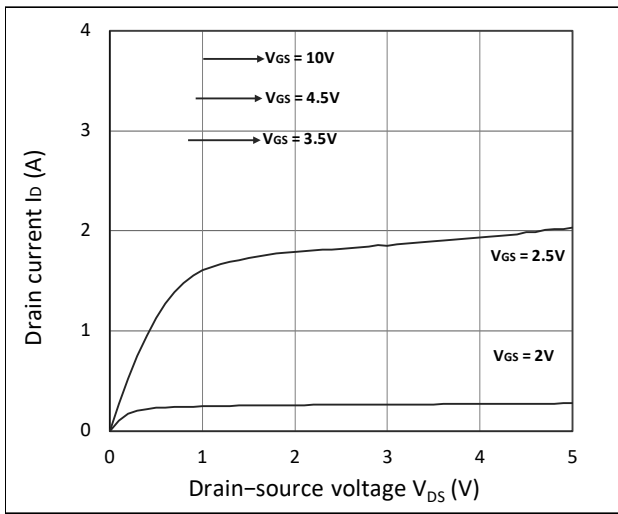


Figure 1. Output Characteristics

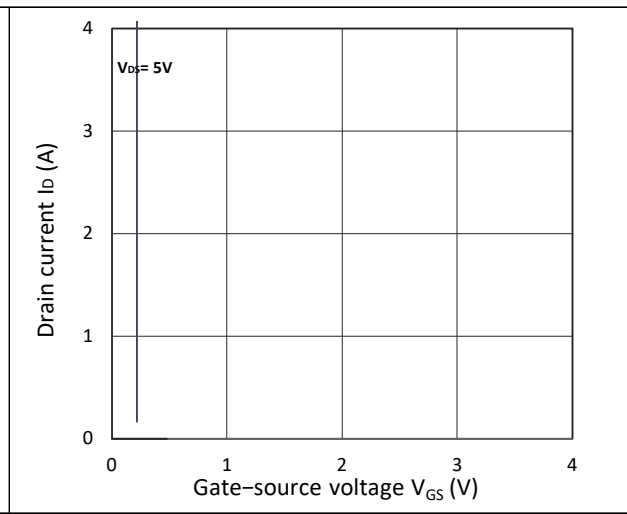


Figure 2. Transfer Characteristics

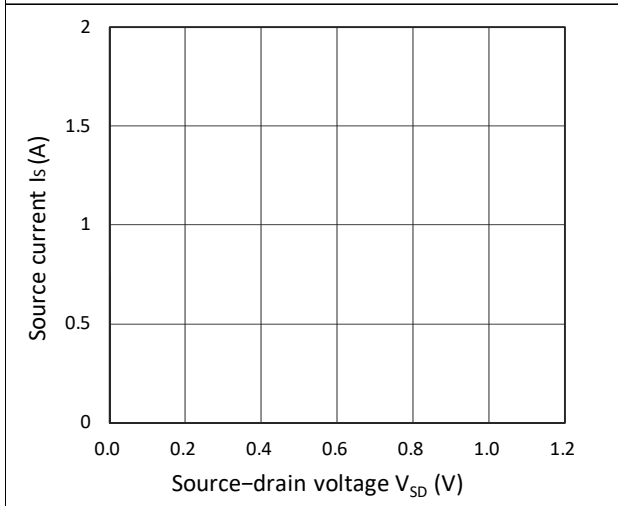


Figure 3. Forward Characteristics of Reverse

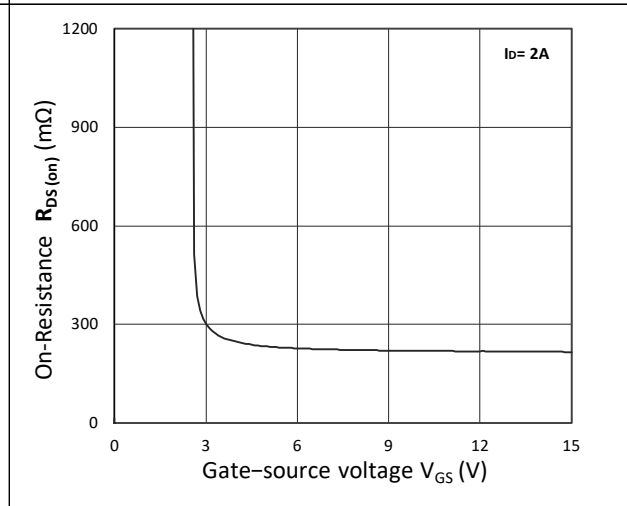


Figure 4. $R_{DS(on)}$ vs. V_{GS}

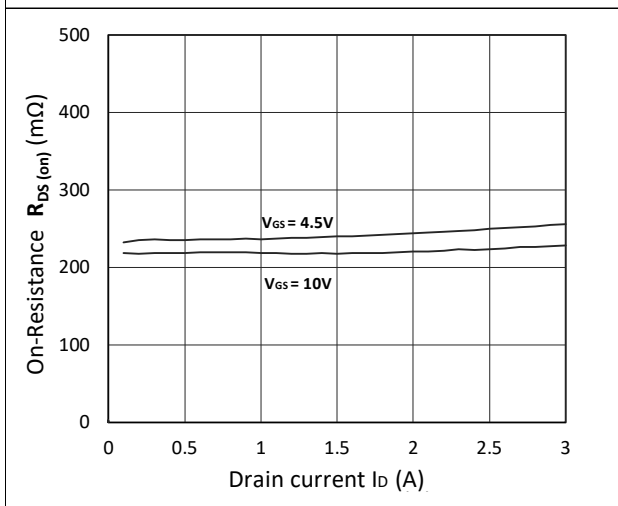


Figure 5. $R_{DS(on)}$ vs. I_D

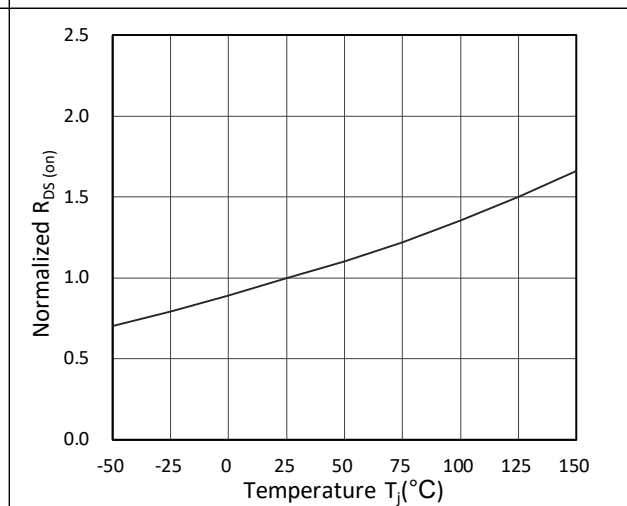


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

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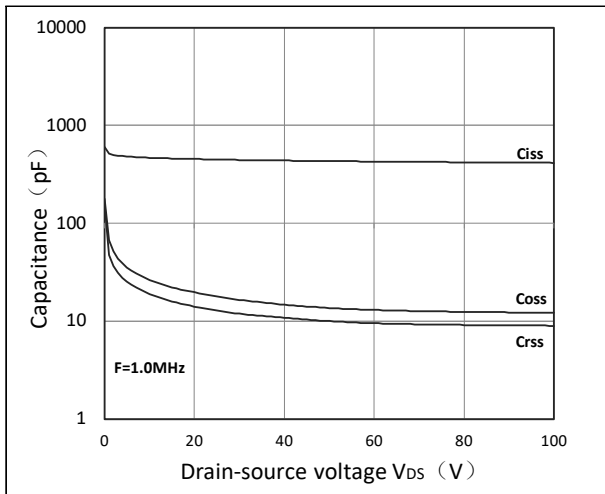


Figure 7. Capacitance Characteristics

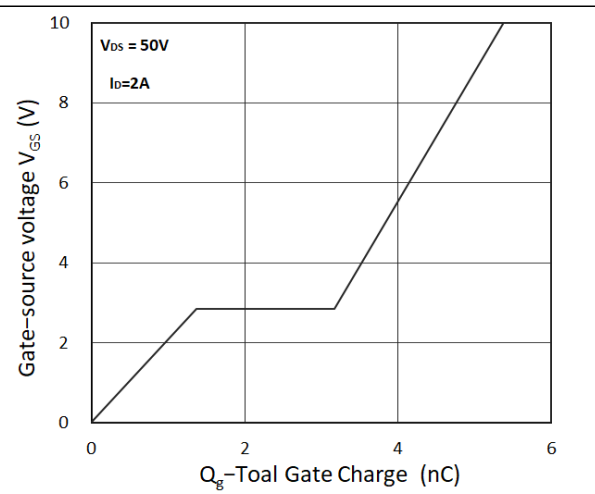
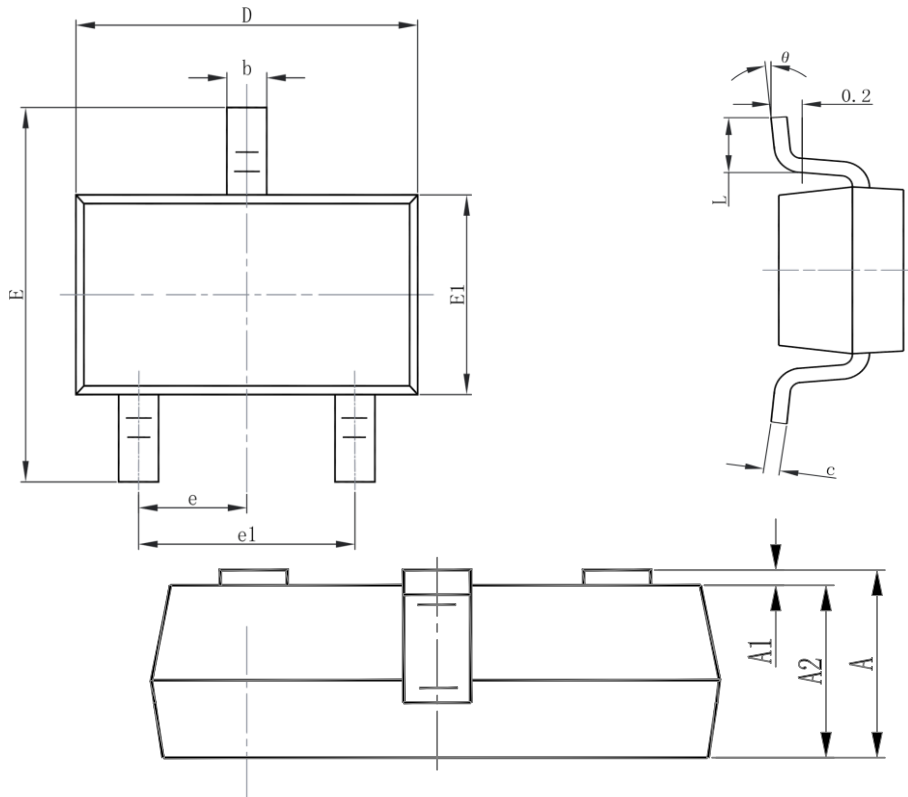


Figure 8. Gate Charge Characteristics

Package Information:SOT-23-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

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